

#### **Vishay Semiconductors**

## **IR Receiver Modules for Remote Control Systems**

#### Description

The TSOP381.. - series are miniaturized receivers for infrared remote control systems. PIN diode and preamplifier are assembled on lead frame, the epoxy package is designed as IR filter.

The demodulated output signal can directly be decoded by a microprocessor. The TSOP381.. series is especially suitable for operation with short burst transmission codes and high data rates.



#### Features

- Photo detector and preamplifier in one package
- Build in filter for carrier frequency of IR signal
- Shielding against electrical field disturbance
- TTL and CMOS compatibility
- · Output active low
- Low power consumption
- Supply voltage range: 2.7 V to 5.5 V
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

#### **Special Features**

- Enhanced datarate of up to 4000 bits/sec.
- Suitable burst length  $\geq$  6 cycles/burst

#### **Mechanical Data**

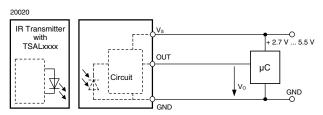
**Pinning:** 

 $1 = OUT, 2 = GND, 3 = V_S$ 

#### **Parts Table**

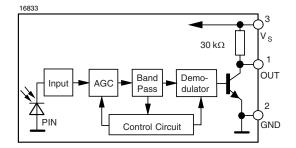
Part	Carrier Frequency		
TSOP38130	30 kHz		
TSOP38133	33 kHz		
TSOP38136	36 kHz		
TSOP38137	36.7 kHz		
TSOP38138	38 kHz		
TSOP38140	40 kHz		
TSOP38156	56 kHz		

## **Application Circuit**



No external components are required

#### **Block Diagram**



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## **Absolute Maximum Ratings**

 $T_{amb} = 25 \ ^{\circ}C$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Supply Voltage	(Pin 3)	V <sub>S</sub>	- 0.3 to + 6.0	V
Supply Current	(Pin 3)	۱ <sub>S</sub>	3	mA
Output Voltage	(Pin 1)	Vo	- 0.3 to (V <sub>S</sub> + 0.3)	V
Output Current	(Pin 1)	Ι <sub>Ο</sub>	10	mA
Junction Temperature		Тj	100	°C
Storage Temperature Range		T <sub>stg</sub>	- 25 to + 85	°C
Operating Temperature Range		T <sub>amb</sub>	- 25 to + 85	°C
Power Consumption	$(T_{amb} \le 85 \ ^{\circ}C)$	P <sub>tot</sub>	30	mW
Soldering Temperature	$t \leq$ 10 s, 1 mm from case	T <sub>sd</sub>	260	°C

## **Electrical and Optical Characteristics**

 $T_{amb} = 25 \ ^{\circ}C$ , unless otherwise specified

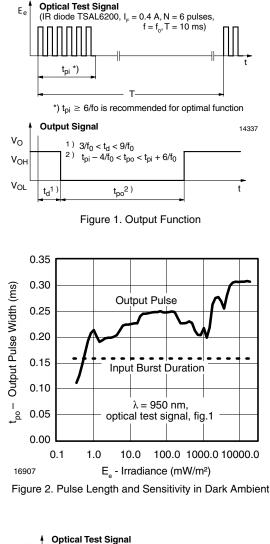
Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Supply Current (Pin 3)	$E_v = 0, V_S = 3.3 V$	I <sub>SD</sub>	1.0	1.3	1.6	mA
	E <sub>v</sub> = 40 klx, sunlight	I <sub>SH</sub>		1.4		mA
Supply Voltage		V <sub>S</sub>	2.7		5.5	V
Transmission Distance	$E_v = 0$ , test signal see fig.1, IR diode TSAL6200, $I_F = 400 \text{ mA}$	d		30		m
Output Voltage Low (Pin 1)	$I_{OSL} = 0.5 \text{ mA}, E_e = 0.7 \text{ mW/m}^2,$ test signal see fig. 1	V <sub>OSL</sub>			250	mV
Minimum Irradiance (30 - 40 kHz)	$V_S = 3 V$ Pulse width tolerance: $t_{pi} - 5/f_o < t_{po} < t_{pi} + 6/f_o$ , test signal see fig.1	E <sub>e min</sub>		0.4	0.6	mW/m <sup>2</sup>
Minimum Irradiance (56 kHz)	$V_S = 3 V$ Pulse width tolerance: $t_{pi} - 5/f_o < t_{po} < t_{pi} + 6/f_o$ , test signal see fig.1	E <sub>e min</sub>		0.5	0.7	mW/m <sup>2</sup>
Minimum Irradiance (30 - 40 kHz)	$V_S = 5 V$ Pulse width tolerance: $t_{pi} - 5/f_o < t_{po} < t_{pi} + 6/f_o$ , test signal see fig.1	E <sub>e min</sub>		0.55	0.7	mW/m <sup>2</sup>
Minimum Irradiance (56 kHz)	$\label{eq:VS} \begin{split} V_S &= 5 \ V \\ \text{Pulse width tolerance:} \\ t_{pi} &- 5/f_o < t_{po} < t_{pi} + 6/f_o, \\ \text{test signal see fig.1} \end{split}$	E <sub>e min</sub>		0.65	0.8	mW/m <sup>2</sup>
Maximum Irradiance	$t_{pi}$ - 5/f <sub>o</sub> < $t_{po}$ < $t_{pi}$ + 6/f <sub>o</sub> , test signal see fig. 1	E <sub>e max</sub>	30			W/m <sup>2</sup>
Directivity	Angle of half transmission distance	φ <sub>1/2</sub>		± 45		deg



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## **Typical Characteristics**

 $T_{amb} = 25$  °C, unless otherwise specified



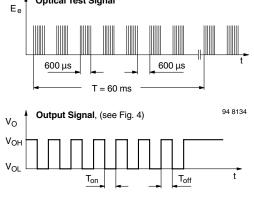
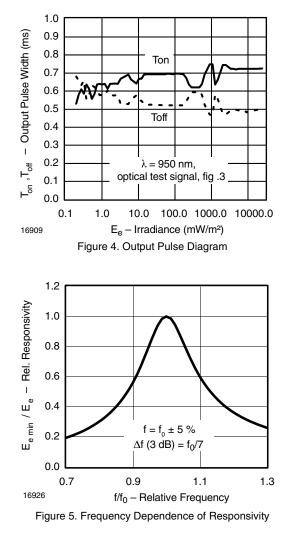
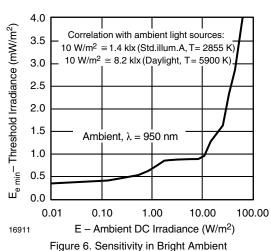


Figure 3. Output Function





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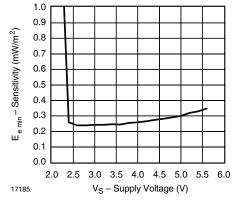


Figure 7. Sensitivity vs. Supply Voltage Disturbances

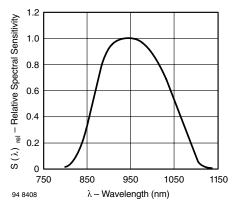


Figure 10. Relative Spectral Sensitivity vs. Wavelength

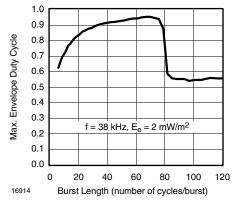


Figure 8. Max. Envelope Duty Cycle vs. Burstlength

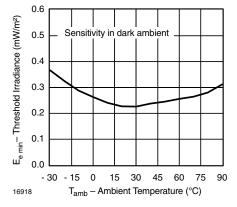
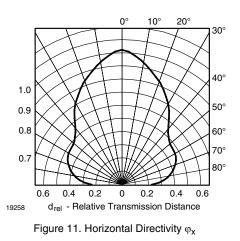


Figure 9. Sensitivity vs. Ambient Temperature



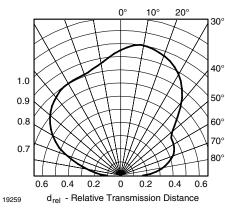


Figure 12. Vertical Directivity  $\phi_y$ 



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#### **Suitable Data Format**

The circuit of the TSOP381.. is designed in that way that unexpected output pulses due to noise or disturbance signals are avoided. A bandpass filter, an integrator stage and an automatic gain control are used to suppress such disturbances.

The distinguishing mark between data signal and disturbance signal are carrier frequency, burst length and duty cycle.

The data signal should fulfill the following conditions:

• Carrier frequency should be close to center frequency of the bandpass (e. g. 38 kHz).

• Burst length should be 6 cycles/burst or longer.

• After each burst which is between 6 cycles and 70 cycles a gap time of at least 10 cycles is necessary.

• For each burst which is longer than 1.8 ms a corresponding gap time is necessary at some time in the data stream. This gap time should have at least same length as the burst.

• Up to 2200 short bursts per second can be received continuously.

Some examples for suitable data format are: NEC Code (repetitive pulse), NEC Code (repetitive data), Toshiba Micom Format, Sharp Code, RC5 Code, RC6 Code, R-2000 Code, Sony Code, RECS-80 Code.

When a disturbance signal is applied to the TSOP381.. it can still receive the data signal. However the sensitivity is reduced to such a level that no unexpected pulses will occur.

Some examples for such disturbance signals which are suppressed by the TSOP381.. are:

• DC light (e.g. from tungsten bulb or sunlight)

• Continuous signal at 38 kHz or at any other frequency

• Signals from fluorescent lamps with electronic ballast (an example of the signal modulation is shown in Figure 13).

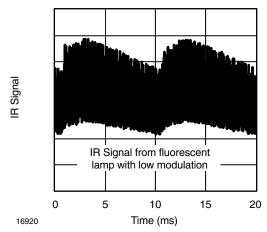
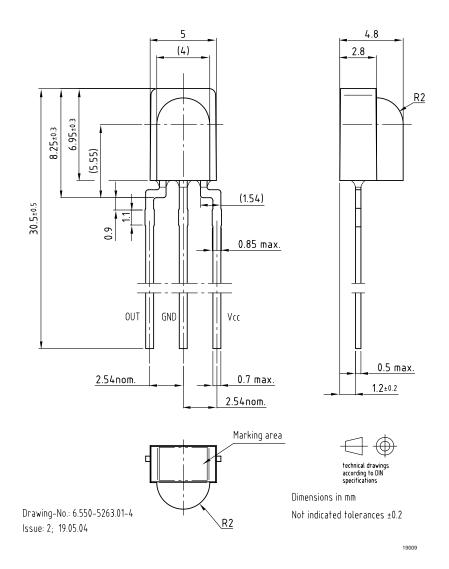


Figure 13. IR Signal from Fluorescent Lamp with low Modulation

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## Package Dimensions in mm





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### **Ozone Depleting Substances Policy Statement**

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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